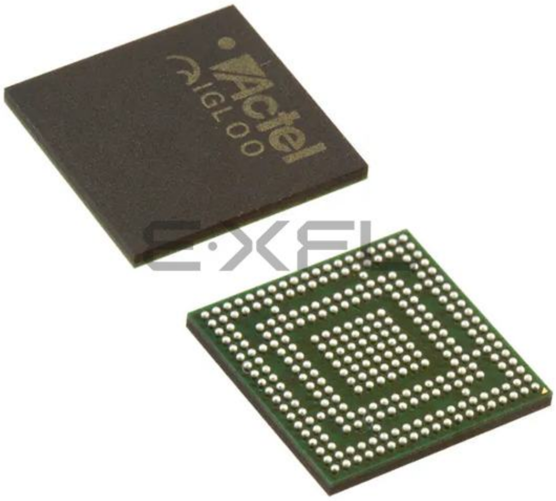
Microchip Technology - AGL1000V5-CS281I Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	24576
Total RAM Bits	147456
Number of I/O	215
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	281-TFBGA, CSBGA
Supplier Device Package	281-CSP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl1000v5-cs281i

Ramping up (V2 devices): 0.65 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.55 V < trip_point_down < 0.95 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V for V5 devices, and 0.75 V ± 0.2 V for V2 devices), the PLL output lock signal goes low and/or the output clock is lost. Refer to the Brownout Voltage section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC®3* and *ProASIC3E* FPGA fabric user guides for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

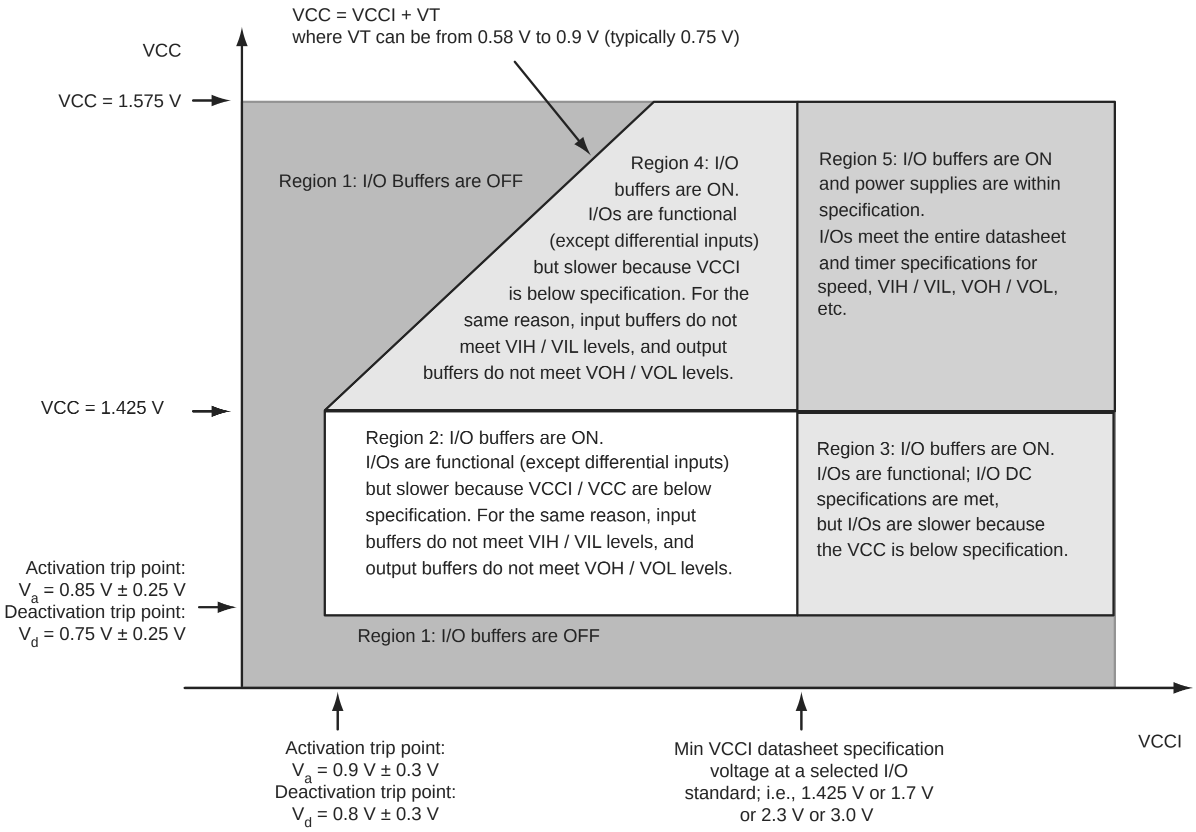


Figure 2-1 • **V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

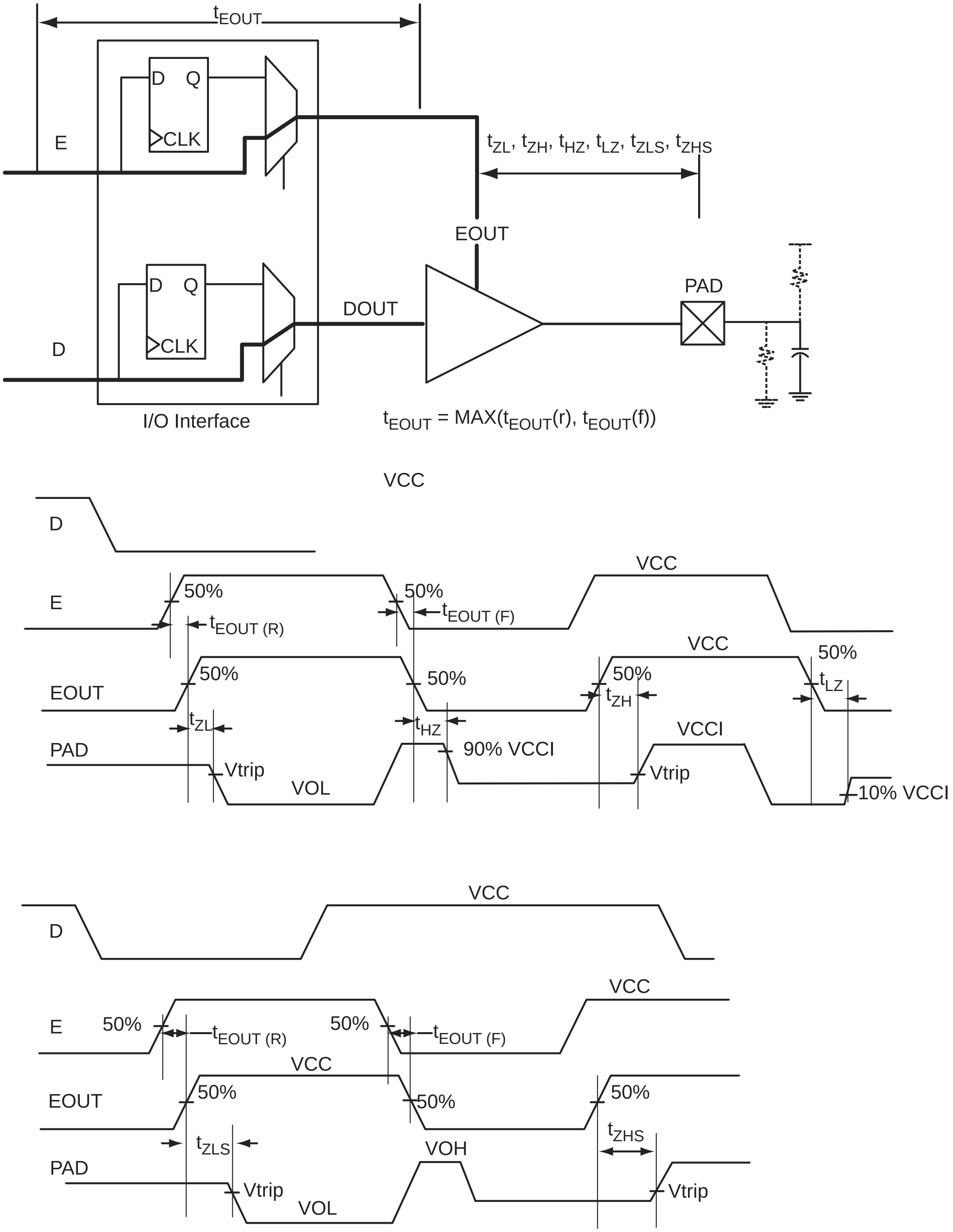


Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (example)**

Table 2-27 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		V_{IH}		VOL	V_{OH}	I_{OL}[1]	I_{OH}[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-54 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
4 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
6 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
8 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
12 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns
16 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-55 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78	ns
4 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78	ns
6 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17	ns
8 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-56 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87	ns
4 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87	ns
6 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
8 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-65 • Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range Applicable to Standard I/O Banks

3.3 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength	Equivalent Software Default Drive Strength Option[1]	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 100°C junction temperature and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

Table 2-66 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Applies to 1.2 V DC Core Voltage

Table 2-73 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	4 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	6 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	8 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	12 mA	Std.	1.55	5.55	0.26	1.32	1.10	5.55	4.96	4.50	5.18	11.34	10.75	ns
100 µA	16 mA	Std.	1.55	5.32	0.26	1.32	1.10	5.32	4.82	4.56	5.29	11.10	10.61	ns
100 µA	24 mA	Std.	1.55	5.19	0.26	1.32	1.10	5.19	4.85	4.63	5.74	10.98	10.63	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-74 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	4 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	6 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	8 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	12 mA	Std.	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
100 µA	16 mA	Std.	1.55	3.67	0.26	1.32	1.10	3.67	2.85	4.57	5.55	9.46	8.64	ns
100 µA	24 mA	Std.	1.55	3.70	0.26	1.32	1.10	3.70	2.79	4.65	6.01	9.49	8.58	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Table 2-77 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI = 2.7 Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	4 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	6 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns
100 µA	8 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-78 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	4 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	6 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
100 µA	8 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

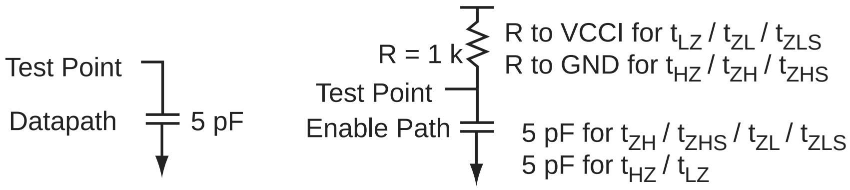


***Figure 2-11* • AC Loading**

***Table 2-130* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.2	0.6	5

Note: **Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.2 V DC Core Voltage

***Table 2-131* • 1.2 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

***Table 2-132* • 1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

***Table 2-133* • 1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

***Table 2-134* • 1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

***Table 2-158* • Input Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.68	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.97	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	1.02	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	1.19	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	1.19	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Output Register

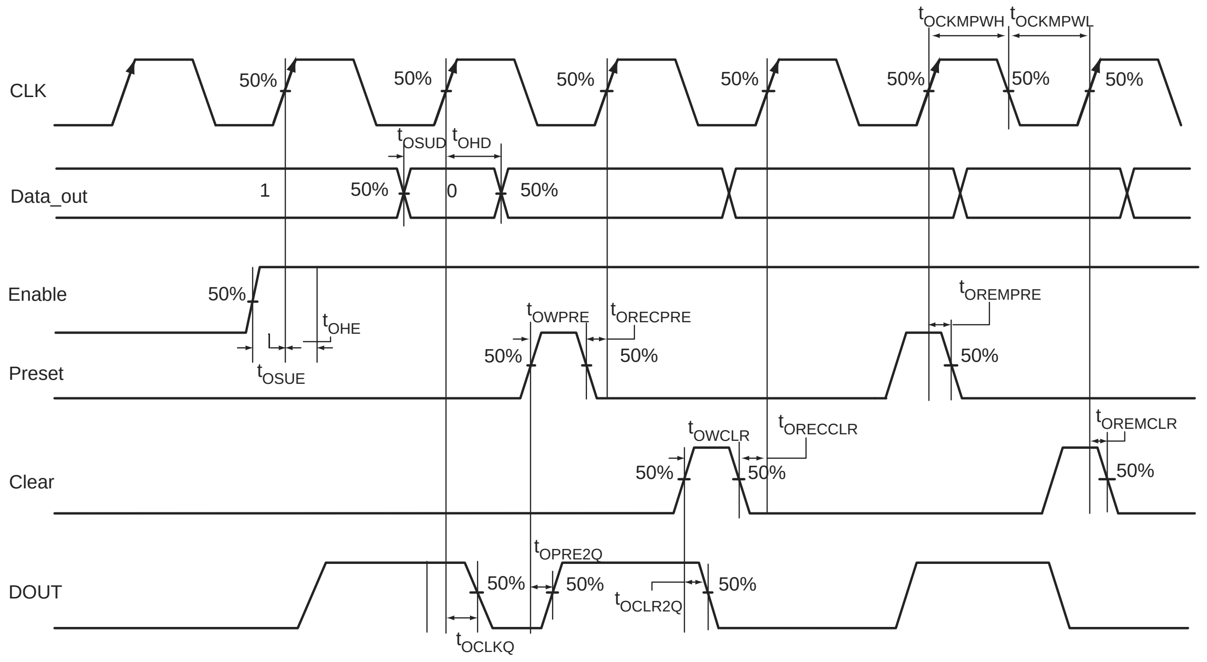


***Figure 2-19* • Output Register Timing Diagram**

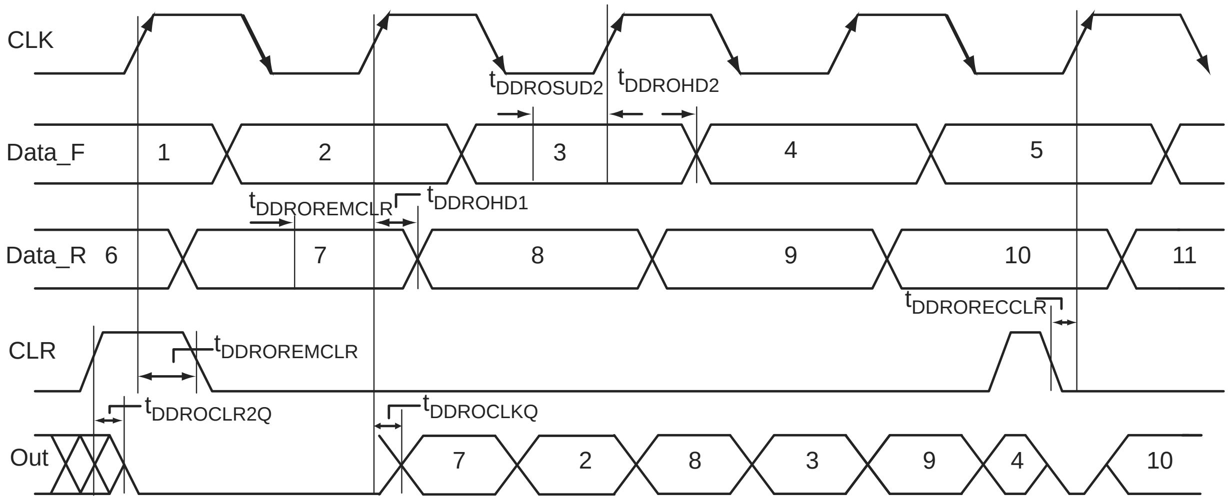


***Figure 2-24* • Output DDR Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-167* • Output DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	1.07	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.67	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.67	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-181 **• AGL015 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.79	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.87	2.26	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-182 **• AGL030 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.80	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.88	2.27	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-187 • AGL600 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.22	2.67	ns
t_{RCKH}	Input High Delay for Global Clock	2.32	2.93	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.61	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-188 • AGL1000 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.31	2.76	ns
t_{RCKH}	Input High Delay for Global Clock	2.42	3.03	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.61	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

***Table 2-193* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN WEN setup time	1.50	ns
t_{ENH}	REN, WEN hold time	0.29	ns
t_{BKS}	BLK setup time	3.05	ns
t_{BKH}	BLK hold time	0.29	ns
t_{DS}	Input data (DIN) setup time	1.33	ns
t_{DH}	Input data (DIN) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	6.61	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	5.72	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	3.38	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.89	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.01	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.86	ns
	RESET Low to data out Low on DOUT (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

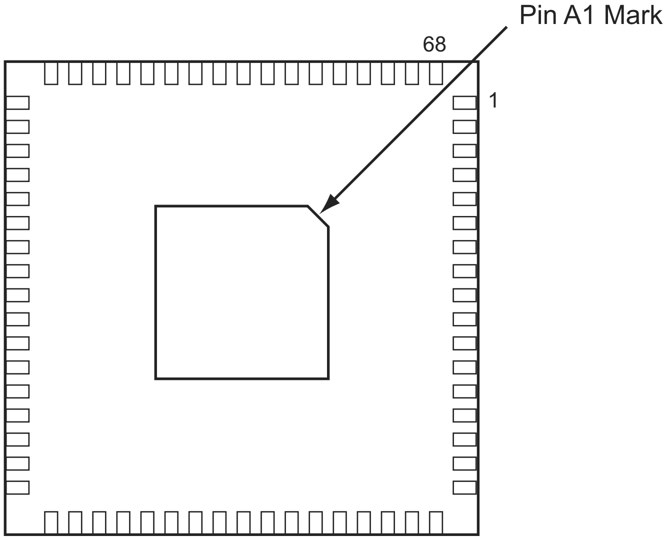
1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

CS196	
Pin Number	**AGL125 Function**
H11	GCB0/IO54RSB0
H12	GCA1/IO55RSB0
H13	IO49RSB0
H14	GCA2/IO57RSB0
J1	GFC2/IO115RSB1
J2	IO110RSB1
J3	IO94RSB1
J4	IO93RSB1
J5	IO89RSB1
J6	NC
J7	VCC
J8	VCC
J9	NC
J10	IO60RSB0
J11	GCB2/IO58RSB0
J12	IO50RSB0
J13	GDC1/IO61RSB0
J14	GDC0/IO62RSB0
K1	IO99RSB1
K2	GND
K3	IO95RSB1
K4	VCCIB1
K5	NC
K6	IO86RSB1
K7	IO80RSB1
K8	IO74RSB1
K9	IO72RSB1
K10	NC
K11	VCCIB0
K12	GDA1/IO65RSB0
K13	GND
K14	GDB1/IO63RSB0
L1	GEB1/IO107RSB1
L2	GEC1/IO109RSB1
L3	GEC0/IO108RSB1
L4	IO96RSB1

CS196	
Pin Number	**AGL125 Function**
L5	IO91RSB1
L6	IO90RSB1
L7	IO83RSB1
L8	IO81RSB1
L9	IO71RSB1
L10	IO70RSB1
L11	VPUMP
L12	VJTAG
L13	GDA0/IO66RSB0
L14	GDB0/IO64RSB0
M1	GEB0/IO106RSB1
M2	GEA1/IO105RSB1
M3	GNDQ
M4	VCCIB1
M5	IO92RSB1
M6	IO88RSB1
M7	NC
M8	VCCIB1
M9	IO76RSB1
M10	GDB2/IO68RSB1
M11	VCCIB1
M12	VMV1
M13	TRST
M14	VCCIB0
N1	GEA0/IO104RSB1
N2	VMV1
N3	GEC2/IO101RSB1
N4	IO100RSB1
N5	GND
N6	IO87RSB1
N7	IO82RSB1
N8	IO78RSB1
N9	IO73RSB1
N10	GND
N11	TCK
N12	TDI

CS196	
Pin Number	**AGL125 Function**
N13	GNDQ
N14	TDO
P1	GND
P2	GEA2/IO103RSB1
P3	FF/GEB2/IO102RSB1
P4	IO98RSB1
P5	IO97RSB1
P6	IO85RSB1
P7	IO84RSB1
P8	IO79RSB1
P9	IO77RSB1
P10	IO75RSB1
P11	GDC2/IO69RSB1
P12	GDA2/IO67RSB1
P13	TMS
P14	GND

QN68



Notes:

1. *This is the bottom view of the package.*
2. *The die attach paddle center of the package is tied to ground (GND).*

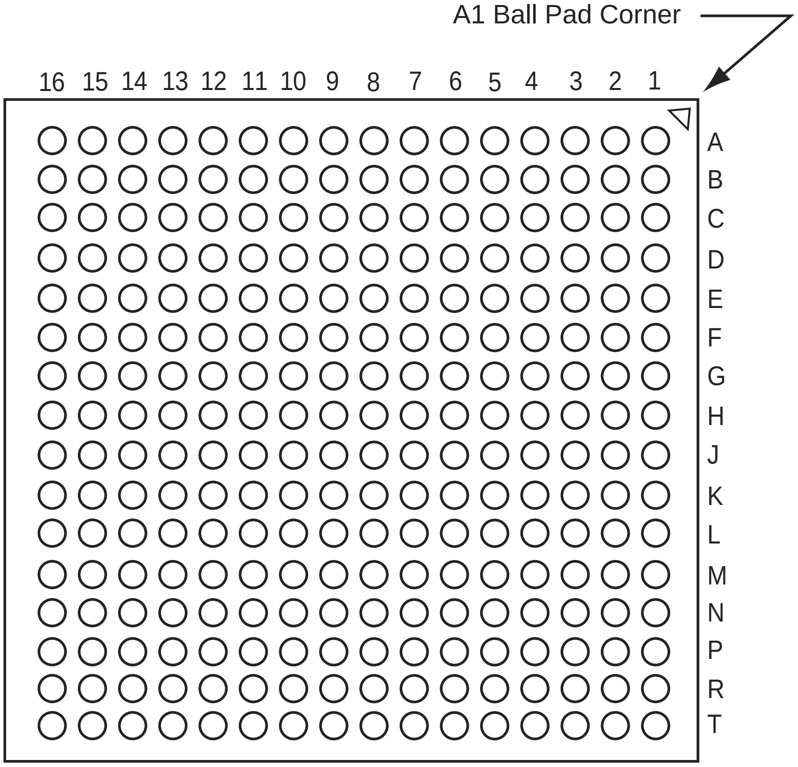
Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG144	
Pin Number	**AGL250 Function**
K1	GEB0/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	**AGL600 Function**
K1	GEB0/IO145NDB3
K2	GEA1/IO144PDB3
K3	GEA0/IO144NDB3
K4	GEA2/IO143RSB2
K5	IO119RSB2
K6	IO111RSB2
K7	GND
K8	IO94RSB2
K9	GDC2/IO91RSB2
K10	GND
K11	GDA0/IO88NDB1
K12	GDB0/IO87NDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO142RSB2
L4	IO136RSB2
L5	VCCIB2
L6	IO115RSB2
L7	IO103RSB2
L8	IO97RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO141RSB2
M3	IO138RSB2
M4	IO123RSB2
M5	IO126RSB2
M6	IO134RSB2
M7	IO108RSB2
M8	IO99RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG484	
Pin Number	**AGL600 Function**
G5	IO171PDB3
G6	GAC2/IO172PDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0
G13	IO40RSB0
G14	IO45RSB0
G15	GNDQ
G16	IO50RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO166PDB3
H5	IO167NPB3
H6	IO172NDB3
H7	IO169NDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO67PPB1
H18	IO64PPB1

Revision	Changes	Page
Revision 23 (December 2012)	The "IGLOO Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43173).	III
	The note in Table 2-189 · IGLOO CCC/PLL Specification and Table 2-190 · IGLOO CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42564). Additionally, note regarding SSOs was added.	2-115, 2-116
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 22 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-2
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40271).	N/A
Revision 21 (May 2012)	Under AGL125, in the Package Pin list, CS121 was incorrectly added to the datasheet in revision 19 and has been removed (SAR 38217).	I to IV
	Corrected the inadvertent error for Max Values for LVPECL VIH and revised the same to '3.6' in Table 2-151 · Minimum and Maximum DC Input and Output Levels (SAR 37685).	2-82
	Figure 2-38 • FIFO Read and Figure 2-39 • FIFO Write have been added (SAR 34841).	2-127
	The following sentence was removed from the VMVx description in the "Pin Descriptions" section: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with “Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks” (SAR 38317). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1